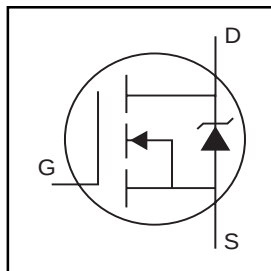


- Logic-Level Gate Drive
- Ultra Low On-Resistance
- Surface Mount (IRLR3303)
- Straight Lead (IRLU3303)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated



$$V_{DS} = 30V$$

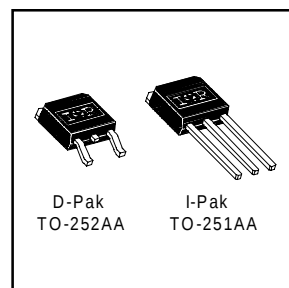
$$R_{DS(on)} = 0.031W$$

$$I_D = 35A⑤$$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



D-Pak
TO-252AA

I-Pak
TO-251AA

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	35 ⑤	A
$I_D @ T_C = 100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	25	
I_{DM}	Pulsed Drain Current ①	140	
$P_D @ T_C = 25^{\circ}C$	Power Dissipation	68	W
	Linear Derating Factor	0.45	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy②	130	mJ
I_{AR}	Avalanche Current①	20	A
E_{AR}	Repetitive Avalanche Energy①	6.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

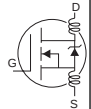
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.2	°C/W
$R_{\theta JA}$	Case-to-Ambient (PCB mount)**	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

** When mounted on 1" square PCB (FR-4 or G-10 Material) .

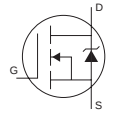
For recommended footprint and soldering techniques refer to application note #AN-994

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$DV_{(BR)DSS}/DT_J$	Breakdown Voltage Temp. Coefficient	—	0.035	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.031	W	$V_{GS} = 10V, I_D = 21A$ ④
		—	—	0.045		$V_{GS} = 4.5V, I_D = 17A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	12	—	—	S	$V_{DS} = 25V, I_D = 20A$ ⑦
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 30V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 24V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	26	nC	$I_D = 20A$
Q_{gs}	Gate-to-Source Charge	—	—	8.8		$V_{DS} = 24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	15		$V_{GS} = 4.5V$, See Fig. 6 and 13 ④ ⑦
$t_{d(on)}$	Turn-On Delay Time	—	7.4	—	ns	$V_{DD} = 15V$
t_r	Rise Time	—	200	—		$I_D = 20A$
$t_{d(off)}$	Turn-Off Delay Time	—	14	—		$R_G = 6.5W, V_{GS} = 4.5V$
t_f	Fall Time	—	36	—		$R_D = 0.70W$, See Fig. 10 ④ ⑦
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact⑥
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	870	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	340	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	170	—		$f = 1.0MHz$, See Fig. 5⑦

**Source-Drain Ratings and Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	35	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	140		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 20A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	72	110	ns	$T_J = 25^\circ\text{C}, I_F = 20A$
Q_{rr}	Reverse Recovery Charge	—	180	280	nC	$di/dt = 100A/\mu s$ ④ ⑦
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
 ② $V_{DD} = 15V$, starting $T_J = 25^\circ\text{C}$, $L = 470\mu H$
 $R_G = 25W$, $I_{AS} = 20A$. (See Figure 12)
 ③ $I_{SD} \leq 20A$, $di/dt \leq 140A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$
 ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

- ⑤ Calculated continuous current based on maximum allowable junction temperature; Package limitation current = 20A.
 ⑥ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact.
 ⑦ Uses IRL3303 data and test conditions.

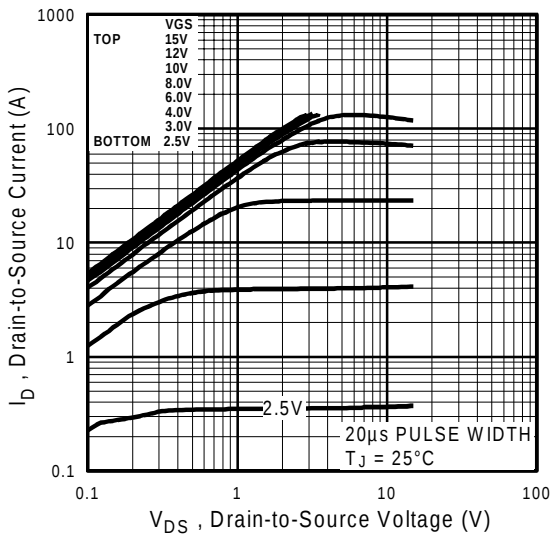


Fig 1. Typical Output Characteristics

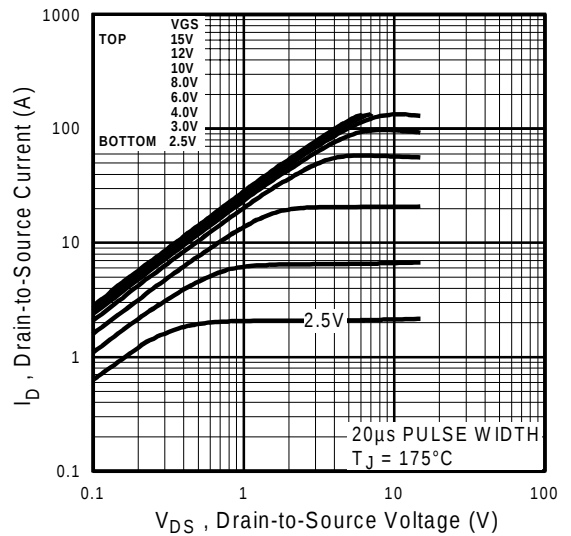


Fig 2. Typical Output Characteristics

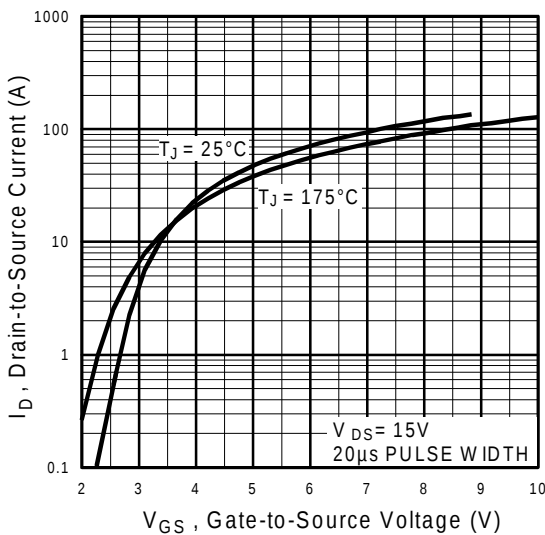


Fig 3. Typical Transfer Characteristics

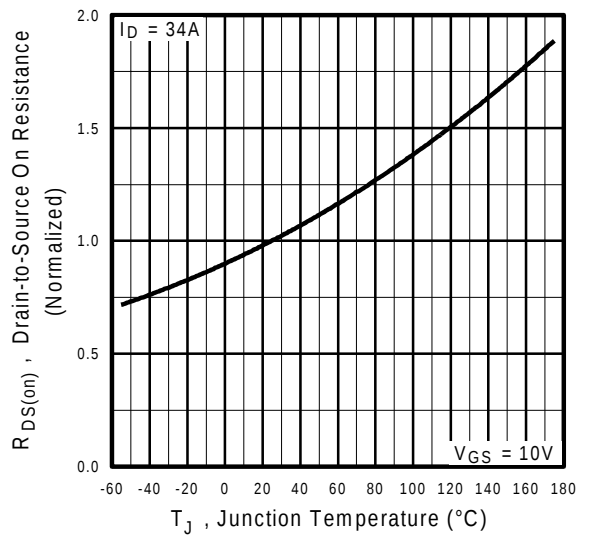


Fig 4. Normalized On-Resistance Vs. Temperature

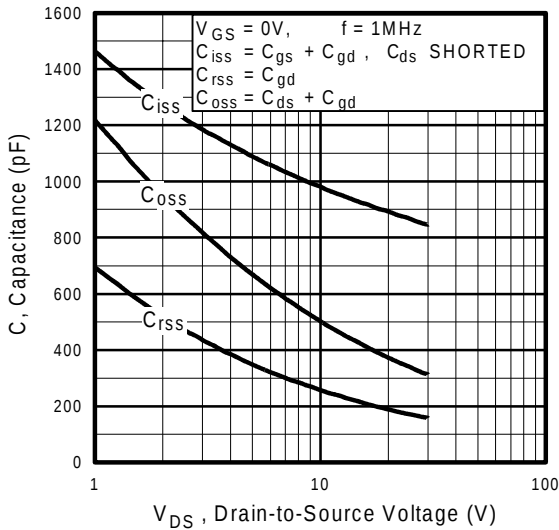


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

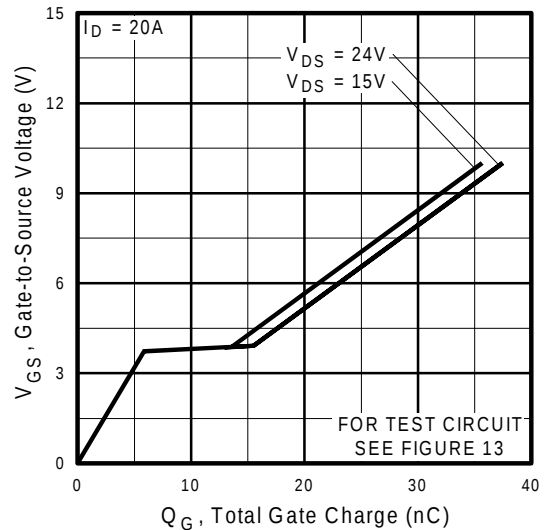


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

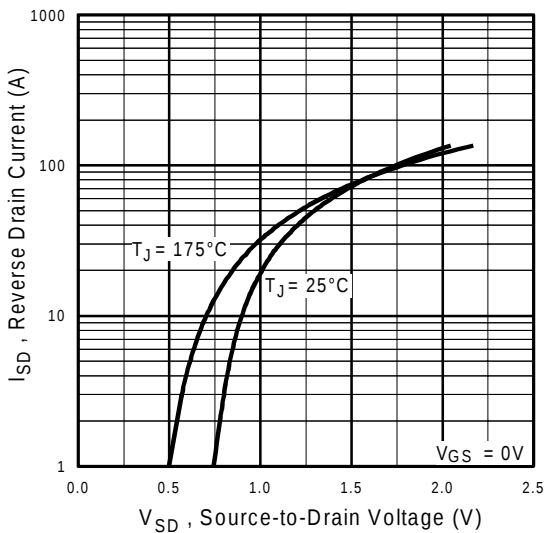


Fig 7. Typical Source-Drain Diode Forward Voltage

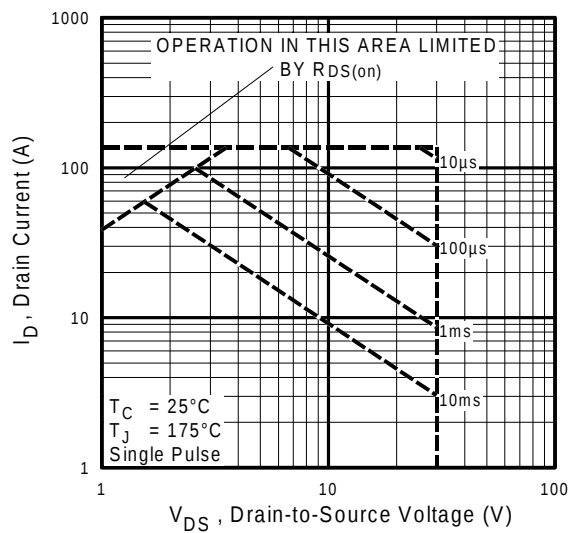


Fig 8. Maximum Safe Operating Area

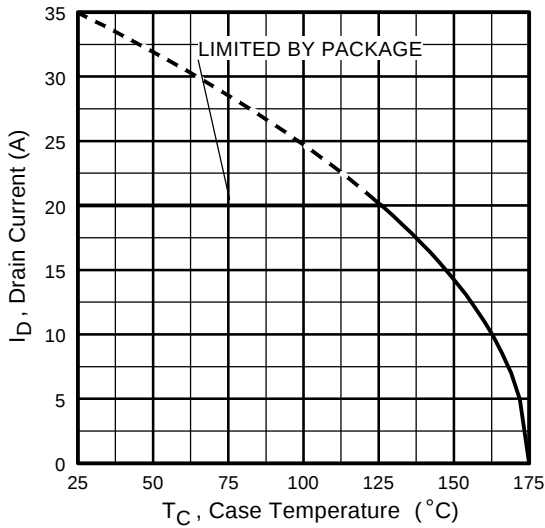


Fig 9. Maximum Drain Current Vs. Case Temperature

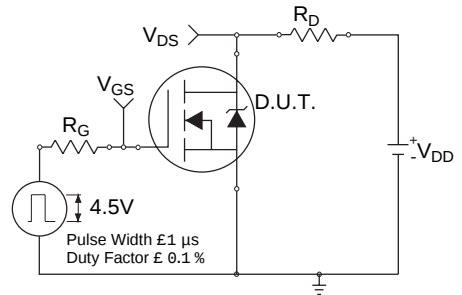


Fig 10a. Switching Time Test Circuit

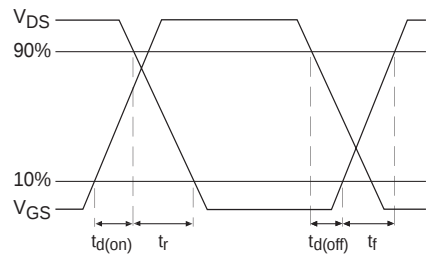


Fig 10b. Switching Time Waveforms

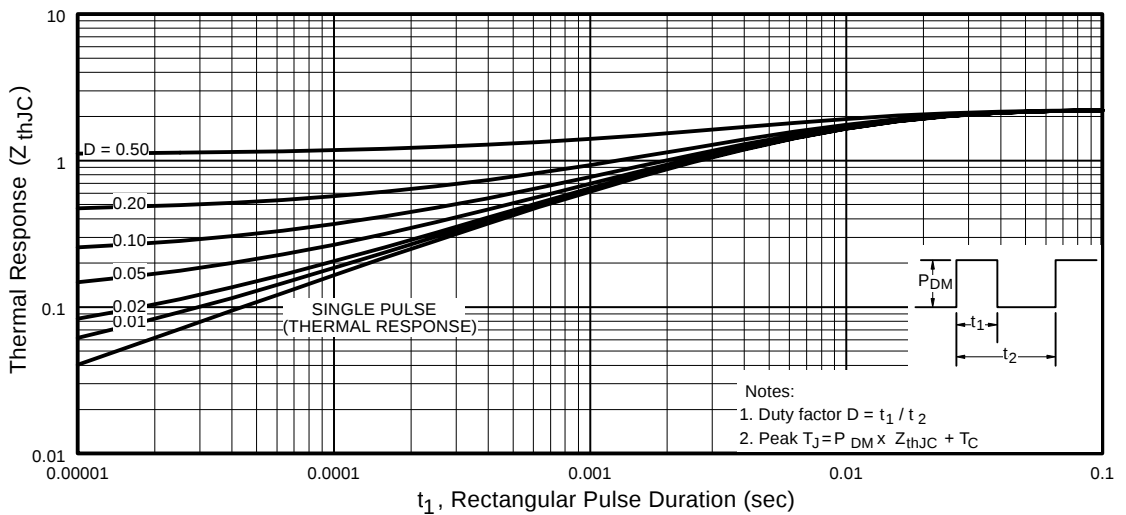
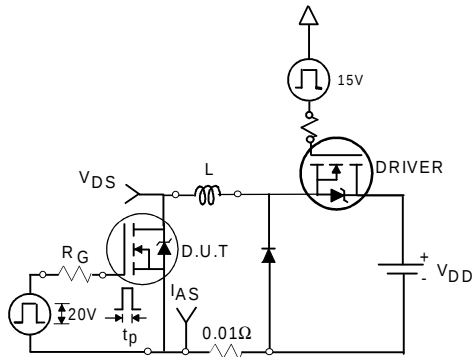
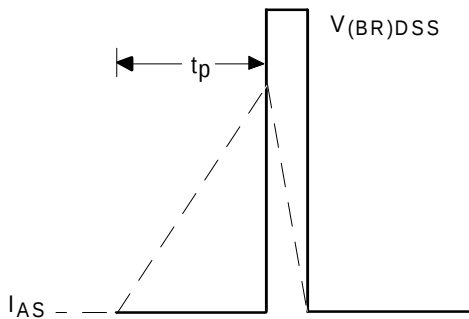
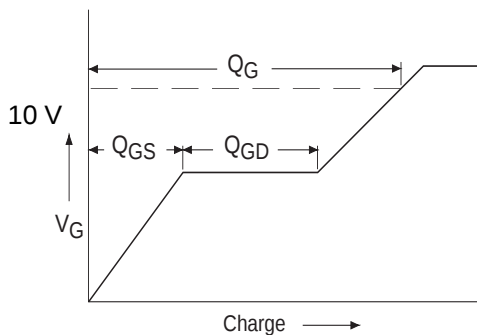
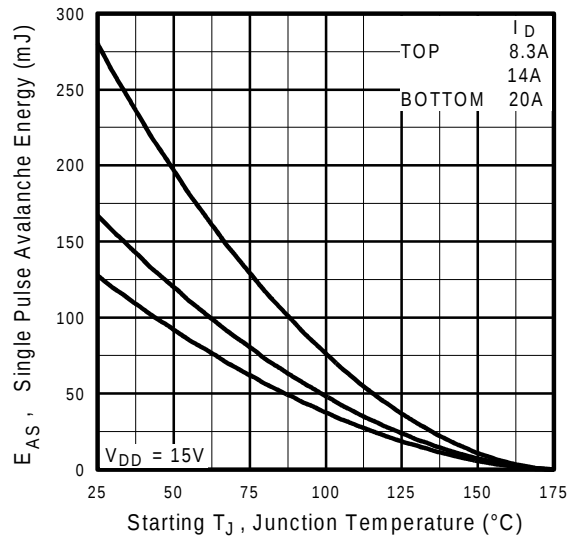
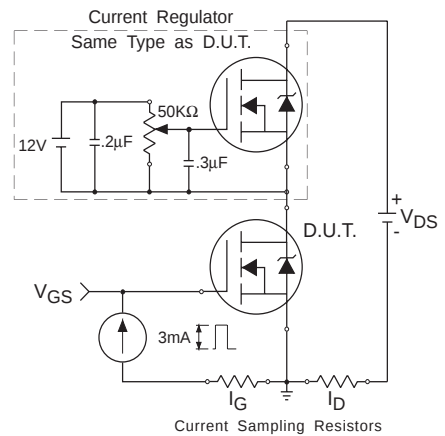
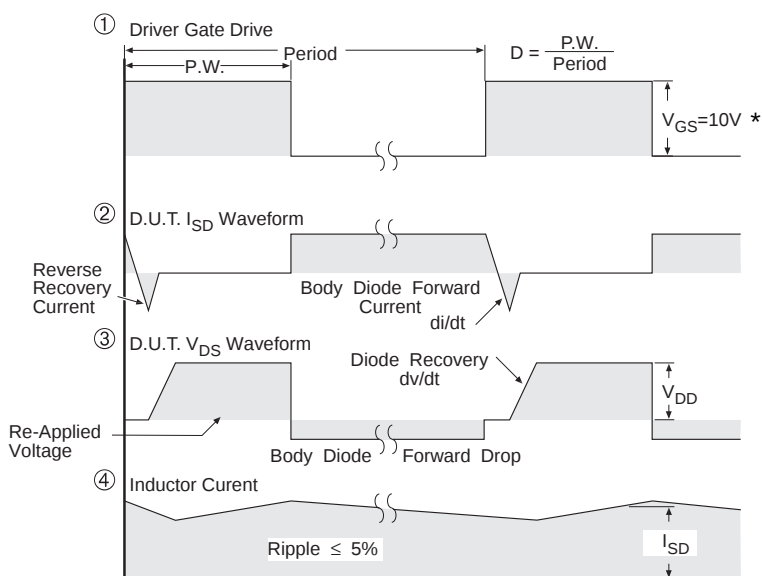
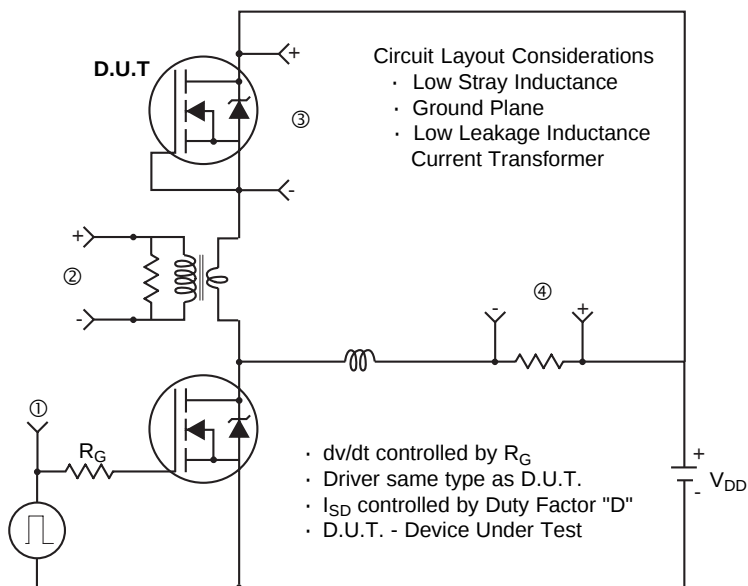


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

**Fig 12a.** Unclamped Inductive Test Circuit**Fig 12b.** Unclamped Inductive Waveforms**Fig 13a.** Basic Gate Charge Waveform**Fig 12c.** Maximum Avalanche Energy
Vs. Drain Current**Fig 13b.** Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

TO-252AA Outline

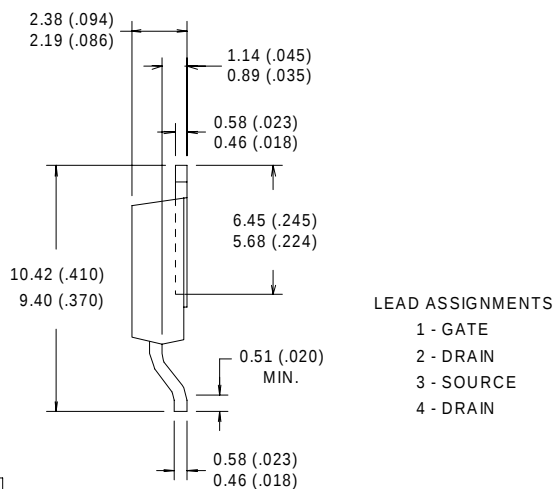
Technical drawing of a mechanical part, likely a connector or plug, showing dimensions in inches and millimeters. The drawing includes a top view (A-A) and a side view (B-B).

Top View (A-A):

- Overall width: 6.73 (.265) inches / 6.35 (.250) inches
- Inner width: 5.46 (.215) inches / 5.21 (.205) inches
- Top flange width: 1.27 (.050) inches / 0.88 (.035) inches
- Top flange height: 6.22 (.245) inches / 5.97 (.235) inches
- Bottom flange width: 1.02 (.040) inches / 1.64 (.025) inches
- Bottom flange height: 1.52 (.060) inches / 1.15 (.045) inches
- Bottom flange diameter: 2X 1.14 (.045) inches / 0.76 (.030) inches
- Bottom flange length: 2.28 (.090) inches

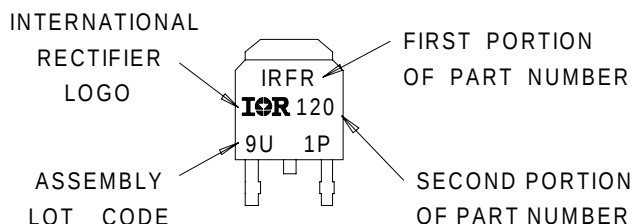
Side View (B-B):

- Overall height: 4.57 (.180) inches
- Inner diameter: 3X 0.89 (.035) inches / 0.64 (.025) inches
- Inner diameter tolerance: 0.25 (.010) inches
- Material: A (M) B



TO-252AA (D-PARK)

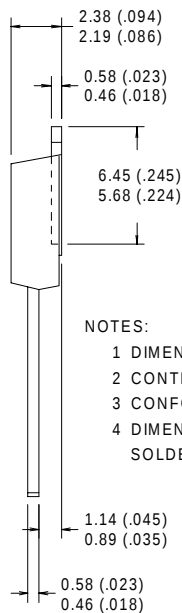
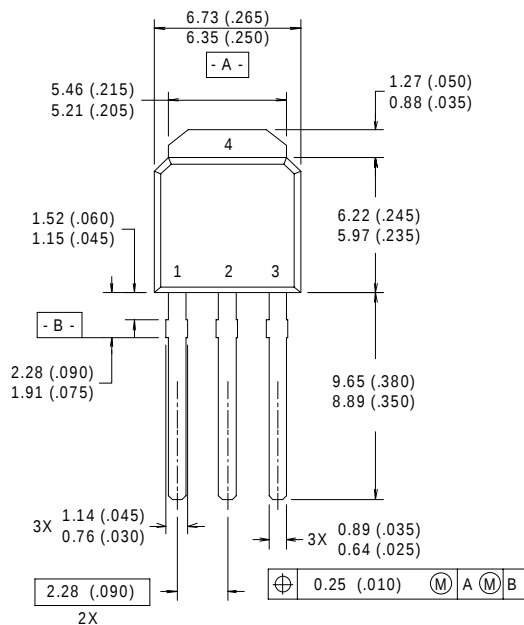
EXAMPLE : THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 9U1P



Package Outline

TO-251AA Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS

- 1 - GATE
2 - DRAIN
3 - SOURCE
4 - DRAIN

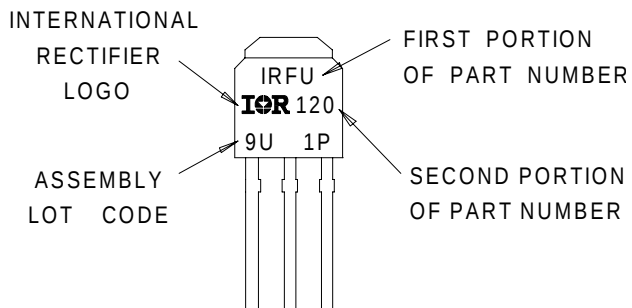
NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH.
3 CONFORMS TO JEDEC OUTLINE TO-252AA.
4 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP,
SOLDER DIP MAX. +0.16 (.006).

Part Marking Information

TO-251AA (I-PARK)

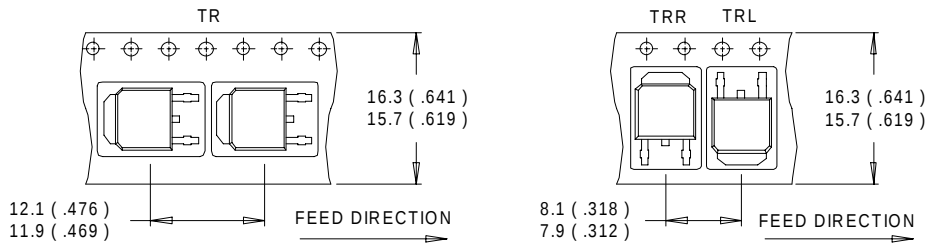
EXAMPLE : THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 9U1P



Tape & Reel Information

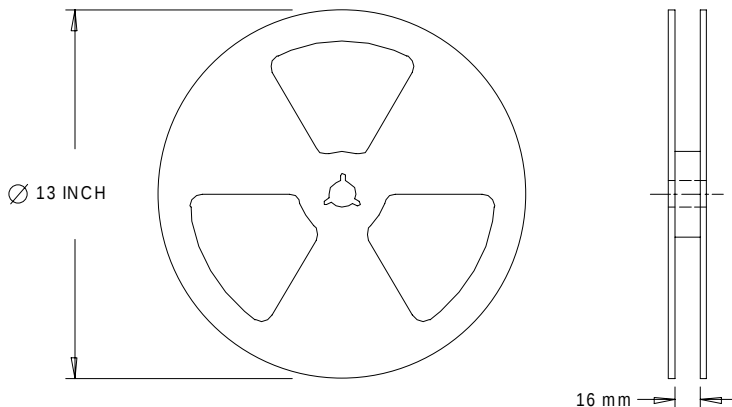
TO-252AA

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

International
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Data and specifications subject to change without notice. 9/98